

MITSUBISHI Nch POWER MOSFET

# FS100VSJ-03

HIGH-SPEED SWITCHING USE

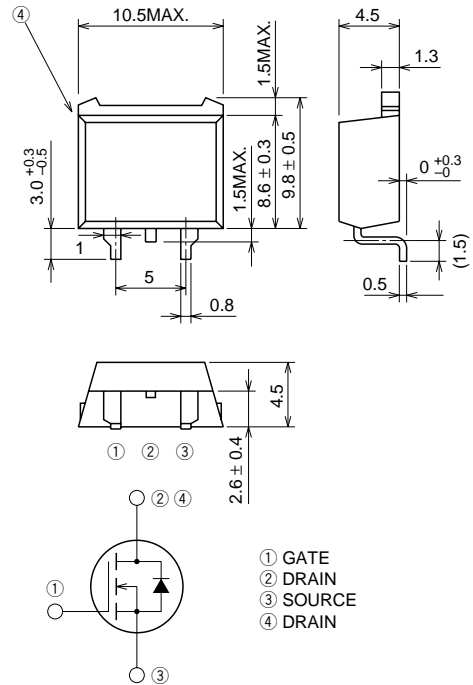
## FS100VSJ-03



- 4V DRIVE
- $V_{DSS}$  ..... 30V
- $r_{DS(ON)}$  (MAX) .....  $4.7m\Omega$
- $I_D$  ..... 100A
- Integrated Fast Recovery Diode (TYP.) ..... 100ns

## OUTLINE DRAWING

Dimensions in mm



TO-220S

## APPLICATION

Motor control, Lamp control, Solenoid control  
DC-DC converter, etc.

## MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
$V_{DSS}$	Drain-source voltage	$V_{GS} = 0V$	30	V
$V_{GSS}$	Gate-source voltage	$V_{DS} = 0V$	$\pm 20$	V
$I_D$	Drain current		100	A
$I_{DM}$	Drain current (Pulsed)		400	A
$I_{DA}$	Avalanche drain current (Pulsed)	$L = 30\mu H$	100	A
$I_S$	Source current		100	A
$I_{SM}$	Source current (Pulsed)		400	A
$P_D$	Maximum power dissipation		125	W
$T_{ch}$	Channel temperature		-55 ~ +150	°C
$T_{stg}$	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	1.2	g

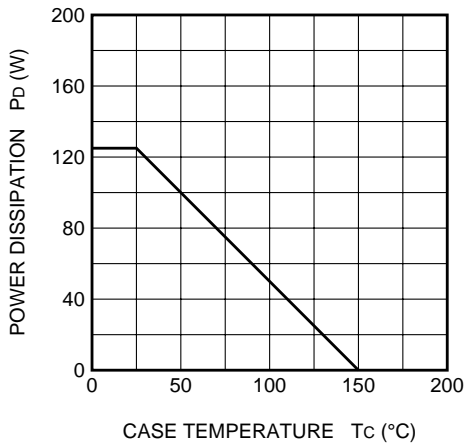
Feb.1999

**ELECTRICAL CHARACTERISTICS** (Tch = 25°C)

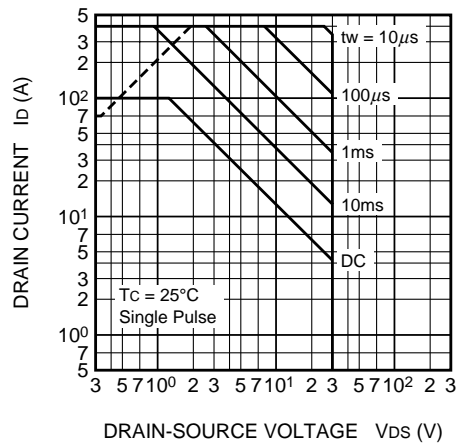
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	ID = 1mA, VGS = 0V	30	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = 30V, VGS = 0V	—	—	0.1	mA
VGS(th)	Gate-source threshold voltage	ID = 1mA, VDS = 10V	1.0	1.5	2.0	V
rDS(ON)	Drain-source on-state resistance	ID = 50A, VGS = 10V	—	3.5	4.7	mΩ
rDS(ON)	Drain-source on-state resistance	ID = 50A, VGS = 4V	—	4.7	8.0	mΩ
VDS(ON)	Drain-source on-state voltage	ID = 50A, VGS = 10V	—	0.175	0.235	V
yfs	Forward transfer admittance	ID = 50A, VDS = 10V	—	80	—	S
Ciss	Input capacitance	VDS = 10V, VGS = 0V, f = 1MHz	—	8000	—	pF
Coss	Output capacitance		—	2250	—	pF
Crss	Reverse transfer capacitance		—	1300	—	pF
td(on)	Turn-on delay time	VDD = 15V, ID = 50A, VGS = 10V, RGEN = RGS = 50Ω	—	55	—	ns
tr	Rise time		—	190	—	ns
td(off)	Turn-off delay time		—	800	—	ns
tf	Fall time		—	470	—	ns
VSD	Source-drain voltage	IS = 50A, VGS = 0V	—	1.0	1.5	V
Rth(ch-c)	Thermal resistance	Channel to case	—	—	1.00	°C/W
trr	Reverse recovery time	IS = 50A, di/dt = -50A/μs	—	100	—	ns

**PERFORMANCE CURVES**

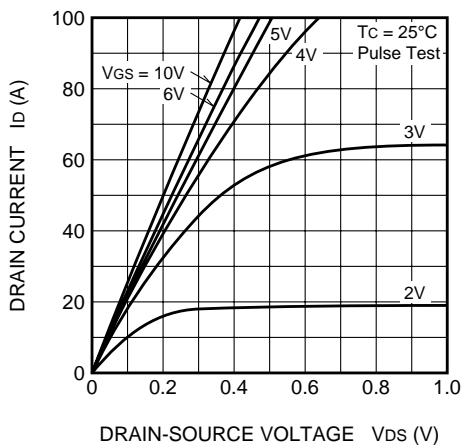
**POWER DISSIPATION DERATING CURVE**



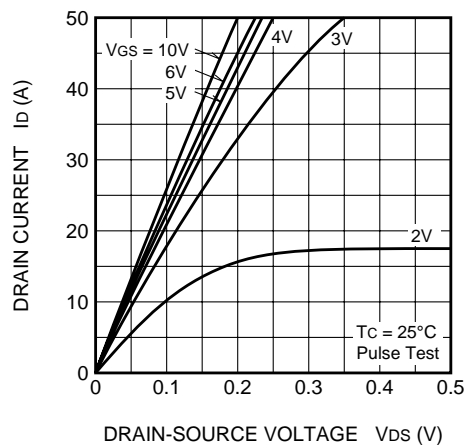
**MAXIMUM SAFE OPERATING AREA**



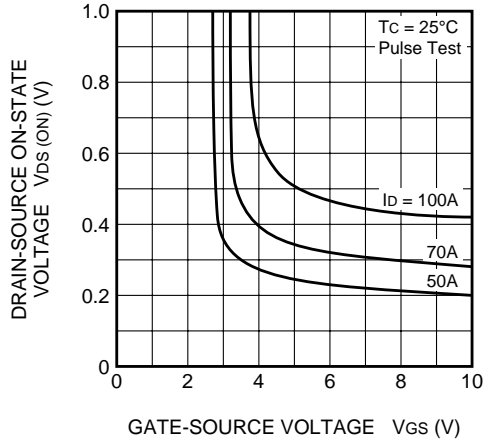
**OUTPUT CHARACTERISTICS (TYPICAL)**



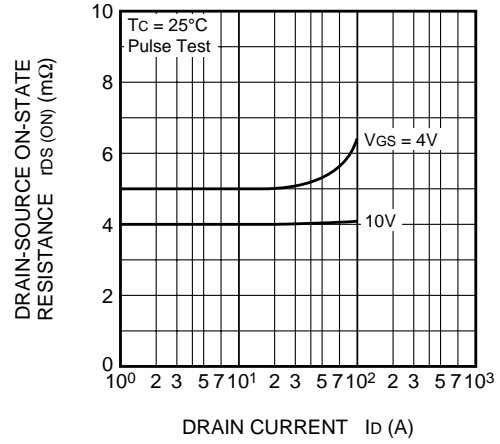
**OUTPUT CHARACTERISTICS (TYPICAL)**



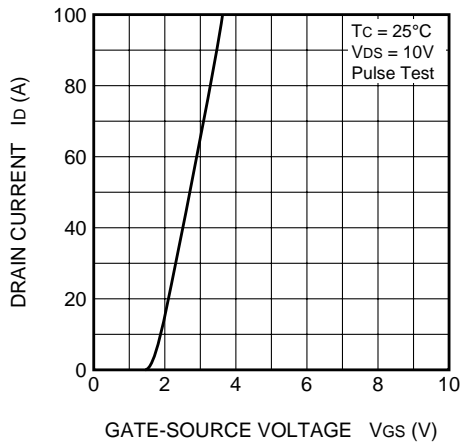
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



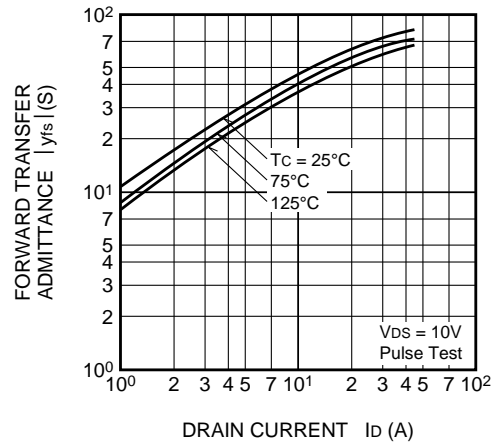
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



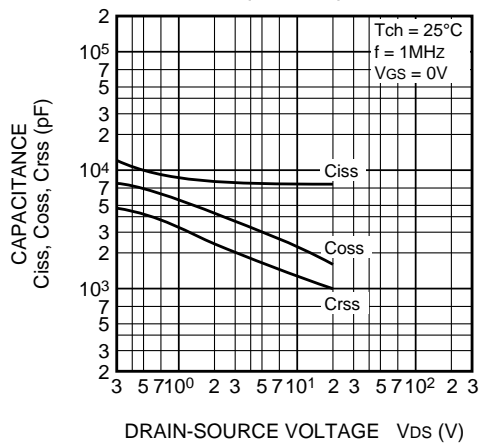
TRANSFER CHARACTERISTICS (TYPICAL)



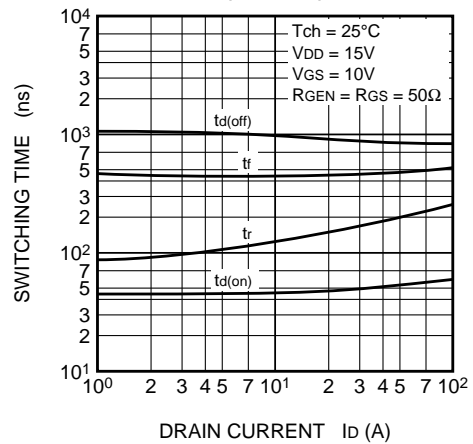
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



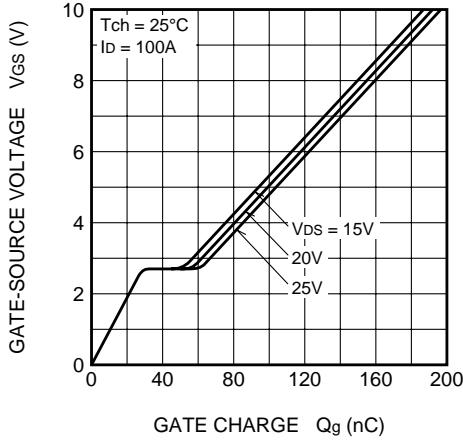
CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



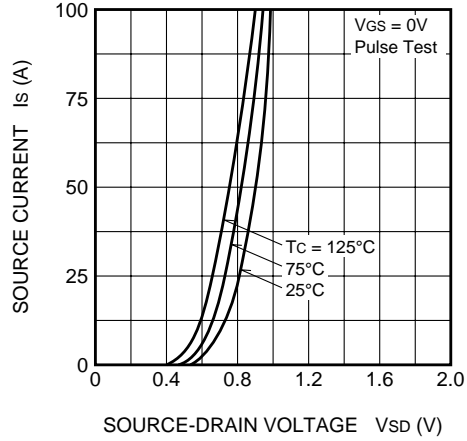
SWITCHING CHARACTERISTICS (TYPICAL)



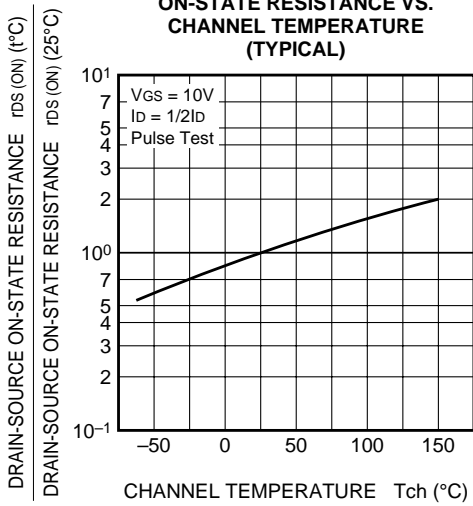
**GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)**



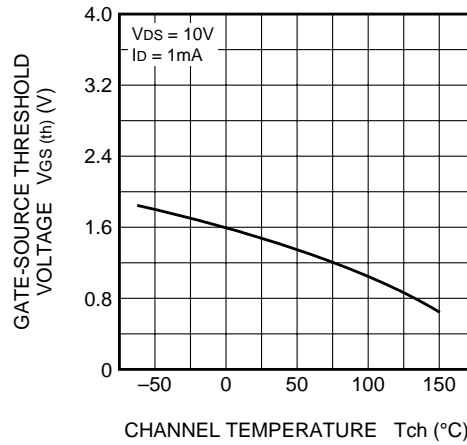
**SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)**



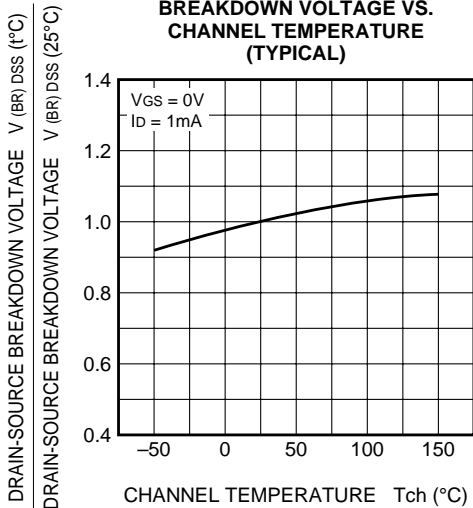
**ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)**



**THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)**



**BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS**

